

## KT9150A

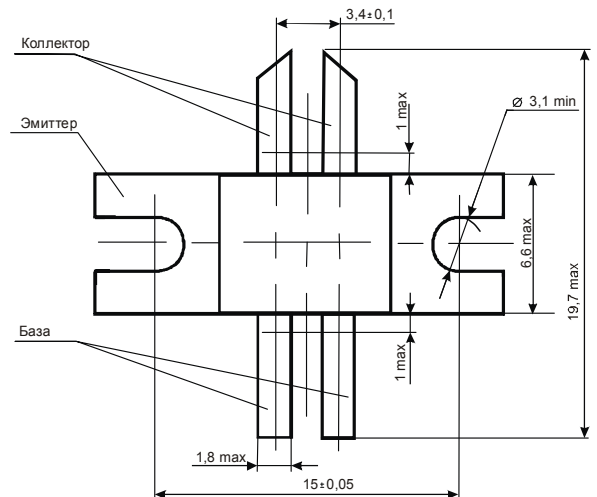
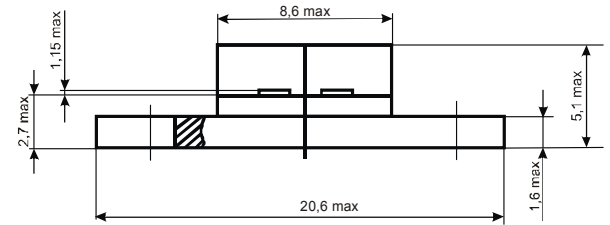
### NPN SILICON RF POWER TRANSISTOR

Designed for operation in ultra - linear Class A low and medium-power amplifiers of TV transmitters (Band IV – V)

- Output power = 8 W (PEP),  $f = 860$  MHz,  $V_{CC} = 25$  V
- Power gain = 8 dB (min)
- 3 Tone IMD = -58 dB (max)

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CER}$	40	V
Emitter-Base Voltage	$V_{EBO}$	4	V
Collector Current	$I_C$	5	A
Operating Junction Temperature	$T_j$	+200	°C
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	2.5	°C/W
Total Power Dissipation, $T_C = 25$ °C	$P_D$	70	W



Case KT-81

#### FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain ( $V_{CC} = 25$ V, $P_{out} = 8$ W PEP, $f = 860$ MHz)	$G_P$	8			dB
Intermodulation Distortion <sup>(2)</sup> ( $V_{CC} = 25$ V, $P_{out} = 8$ W PEP, $f = 860$ MHz)	3 Tone IMD			-58	dB

NOTE: Three-tone test method (vision carrier: -8dB, sound carrier: -7dB, sideband carrier: -16dB)

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Specification is subject to change without notice